TOSHIBA Field Effect Transistor Silicon P Channel MOS Type (U-MOS V)

# **TPCM8102**

Lithium Ion Battery Applications
Notebook PC Applications
Portable Equipment Applications

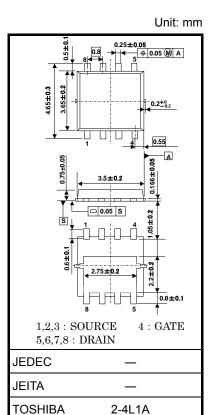
• Small footprint due to a small and thin package

• Low drain-source ON-resistance:  $RDS(ON) = 6.0 \text{ m}\Omega \text{ (typ.)}$ 

- High forward transfer admittance:  $|Y_{fs}| = 44S$  (typ.)
- Low leakage current:  $IDSS = -10 \mu A \text{ (max) (VDS} = -30 \text{ V)}$
- Enhancement mode:  $V_{th}$  = -0.8 to -2.0 V ( $V_{DS}$  = -10 V,  $I_{D}$  = -1 mA)

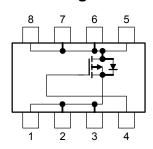
### Absolute Maximum Ratings (Ta = 25°C)

Characte	eristic	Symbol	Rating	Unit	
Drain-source voltage		$V_{DSS}$	-30	V	
Drain-gate voltage (R	$k_{GS} = 20 \text{ k}\Omega$	$V_{DGR}$	-30	V	
Gate-source voltage		V <sub>GSS</sub>	±20	V	
Drain current	DC (Note 1)	ID	-25	А	
Drain current	Pulse (Note 1)	I <sub>DP</sub>	-75 30	^	
Drain power dissipation	on (Tc = 25°C)	$P_{D}$	30	W	
Drain power dissipation	on $(t = 10 s)$ (Note 2a)	$P_{D}$	2.3	W	
Drain power dissipation	on (t = 10 s) (Note 2b)	P <sub>D</sub>	1.0	W	
Single-pulse avalanch	ne energy (Note 3)	E <sub>AS</sub>	81	mJ	
Avalanche current		I <sub>AR</sub>	-25	Α	
Repetitive avalanche	energy = 25°C) (Note 4)	E <sub>AR</sub>	1.8	mJ	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature	range	T <sub>stg</sub>	–55 to 150	°C	



Weight: 0.028 g (typ.)

#### **Circuit Configuration**



Note: For Notes 1 to 4, refer to the next page.

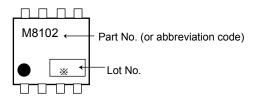
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.

#### **Thermal Characteristics**

Characteristic	Symbol	Max	Unit
Thermal resistance, channel to case $(\mbox{Tc} = 25\mbox{°C}) \label{eq:Tc}$	R <sub>th (ch-c)</sub>	4.17	°C/W
Thermal resistance, channel to ambient $(t = 10 \text{ s})$ (Note 2a)	R <sub>th (ch-a)</sub>	54.3	°C/W
Thermal resistance, channel to ambient $(t = 10 \text{ s})$ (Note 2b)	R <sub>th (ch-a)</sub>	125	°C/W

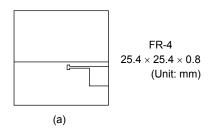
### Marking (Note 5)

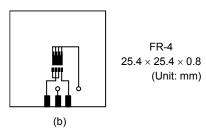


Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a)

(b) Device mounted on a glass-epoxy board (b)



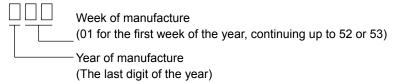


Note 3:  $V_{DD} = -24~V$ ,  $T_{ch} = 25^{\circ}C$  (initial),  $L = 100 \mu H$ ,  $R_G = 25~\Omega$ ,  $I_{AR} = -25~A$ 

Note 4: Repetitive rating: pulse width limited by max channel temperature

Note 5: • on lower left of the marking indicates Pin 1.

\* Weekly code: (Three digits)



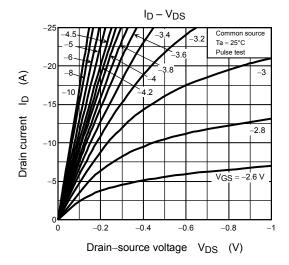
# Electrical Characteristics (Ta = 25°C)

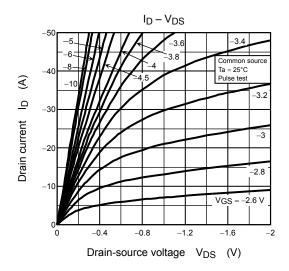
Ch	Characteristic		Test Condition	Min	Тур.	Max	Unit
Gate leakage cur	rent	I <sub>GSS</sub>	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±100	nA
Drain cutoff curre	ent	I <sub>DSS</sub>	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$	_	_	-10	μА
Drain source bro	akdown voltago	V <sub>(BR)DSS</sub>	$I_D = -10 \text{ mA}, V_{GS} = 0 \text{ V}$	-30	_	_	V
Diam-source bre	akdowii vollage	V <sub>(BR)DSX</sub>	$I_D = -10 \text{ mA}, V_{GS} = 20 \text{ V}$	-13	_	_	v
Gate threshold vo	oltage	V <sub>th</sub>	$V_{DS} = -10 \text{ V}, I_D = -1 \text{ mA}$	-0.8 — -2.0		-2.0	V
Drain-source ON-resistance Forward transfer admittance		R <sub>DS</sub> (ON)	$V_{GS} = -4 \text{ V}, I_D = -12 \text{ A}$	_	11	16	- mΩ
			$V_{GS} = -10 \text{ V}, I_D = -12 \text{ A}$	_	6.0	7.7	
Forward transfer admittance		Y <sub>fs</sub>	$V_{DS} = -10 \text{ V}, I_D = -12 \text{ A}$	22	44	_	S
Input capacitance		C <sub>iss</sub>		_	2450	_	pF
Reverse transfer capacitance		C <sub>rss</sub>	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{MHz}$	_	530	_	
Output capacitance		Coss		_	740	_	
	Rise time	t <sub>r</sub>	$V_{GS}$ $0 \text{ V}$ $\Gamma$ $I_{D} = -12 \text{ A}$	_	13	_	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	_	ns					
	Fall time	t <sub>f</sub>	₩.	_	145	_	
	Turn-off time	t <sub>off</sub>		ı	340	ı	
0		Qg	Vpp ≈ -24 V Vcs = -10 V	_	60	_	
Gate-source charge 1		Q <sub>gs1</sub>	, 00	_	11	_	nC
Gate-drain ("Miller") charge		Q <sub>gd</sub>		_	19	_	

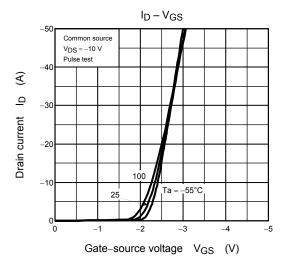
## **Source-Drain Ratings and Characteristics (Ta = 25°C)**

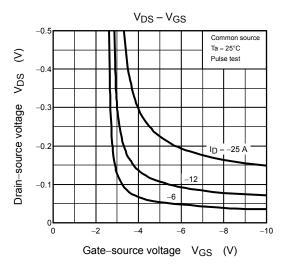
Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit	
Drain reverse current	Pulse	(Note 1)	I <sub>DRP</sub>	_	_	_	-75	Α
Forward voltage (diode)			V <sub>DSF</sub>	$I_{DR} = -25 \text{ A}, V_{GS} = 0 \text{ V}$	_	_	1.2	V

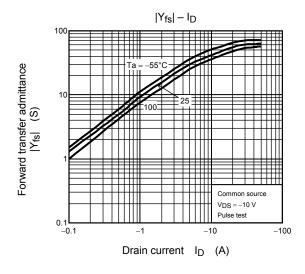
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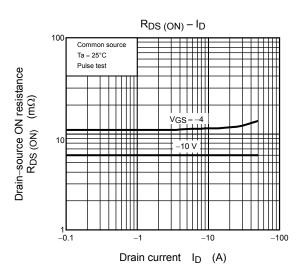




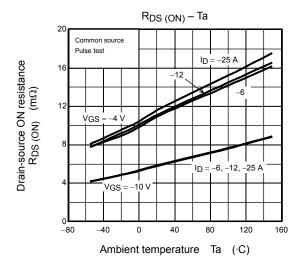


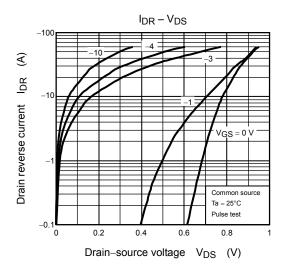


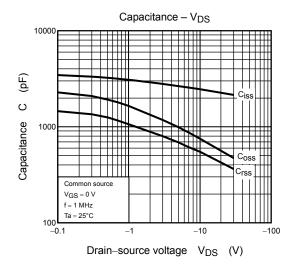


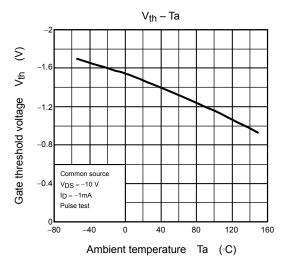


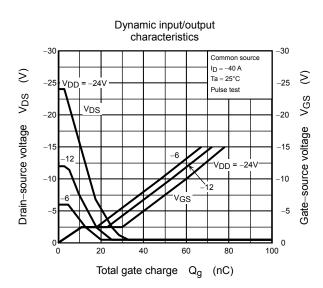
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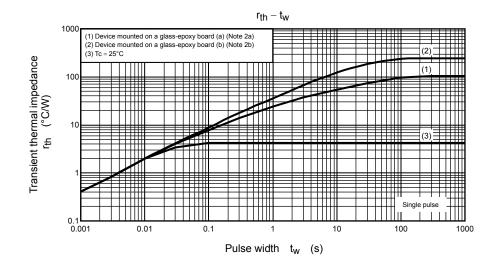


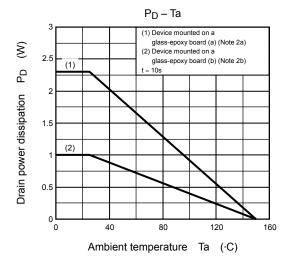


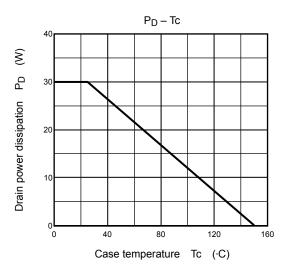


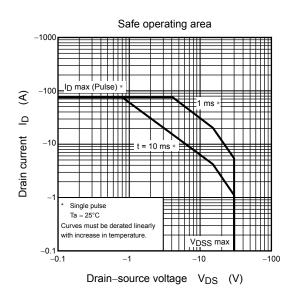


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